SK2302A

Feature

- 16V/3.6A, $R_{DS(ON)}$ = 80m Ω (MAX) @V_{GS}= 4.5V.
  $R_{DS(ON)}$ = 90m Ω (MAX) @V_{GS}= 2.5V.
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- SC-59 for Surface Mount Package.

SC-59

Applications

- Power Management
  Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings T_A=25℃ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	16	V
Gate-Source Voltage	V_{GS}	±8	V
Drain Current-Continuous	I_D	3.6	A

Electrical Characteristics T_A=25℃ Unless Otherwise noted

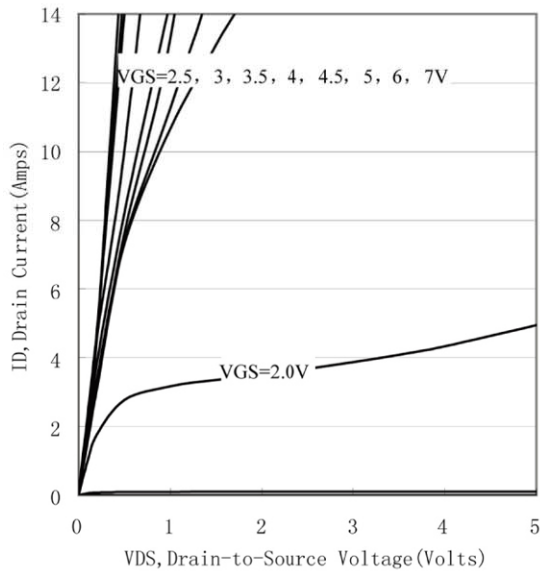| Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=250 μA	16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=12V, VGS=0V	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=8V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=−8V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=250μA	0.4	-	1.3	V
Static Drain-source On-Resistance	RDS(ON)	VGS =4.5V, ID =3.6A	-	70	80	m Ω
		VGS =2.5V, ID =3.1A	-	75	90	m Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=0.94A			1.2	V

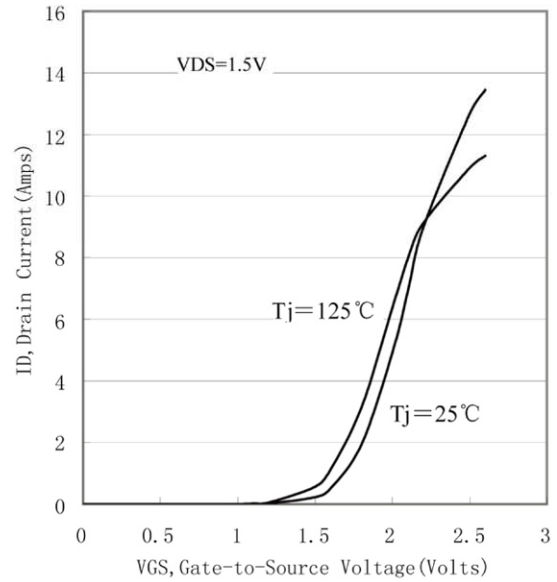## Typical Characteristics

Figure 1. Output Characteristics

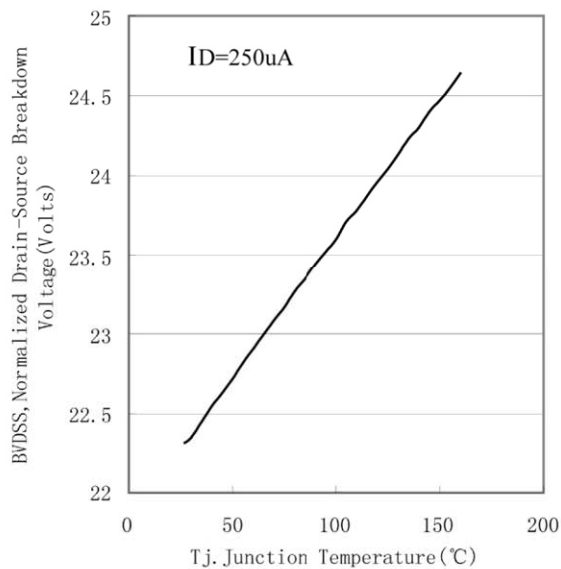Figure 2. Transfer Characteristics

Figure 3. Breakdown Voltage Variation
with Temperature

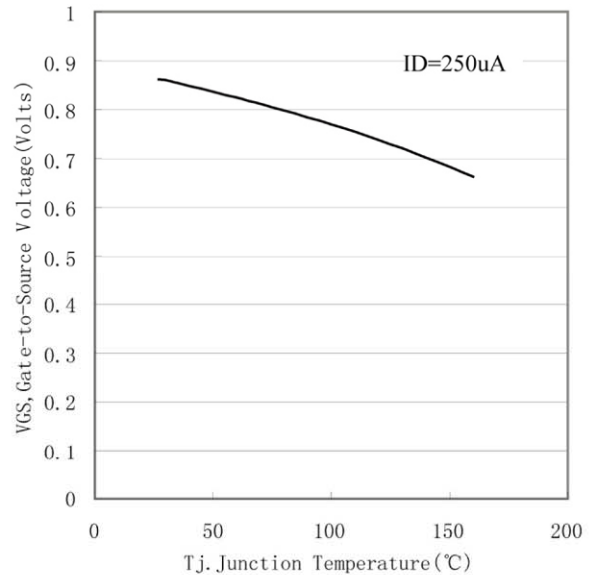Figure 4. Gate Threshold Variation
with Temperature

www.shike.tw

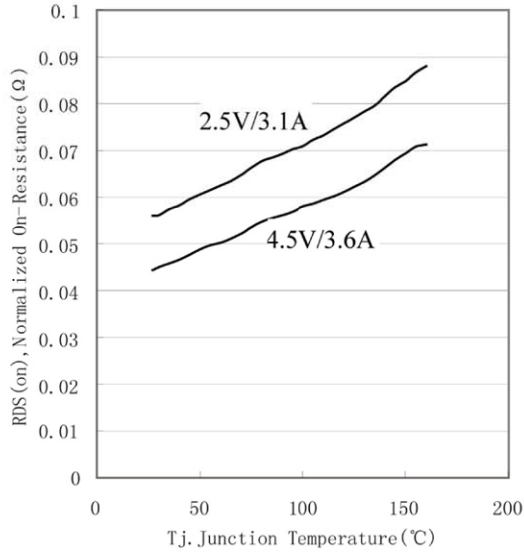## Typical Characteristics

Figure 5. On-Resistance Variation
with Temperature
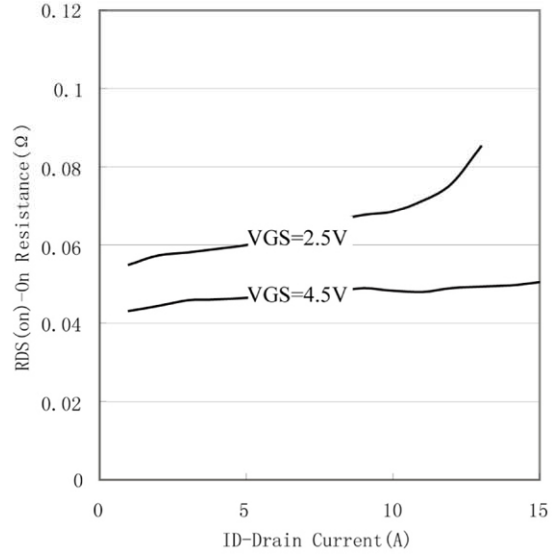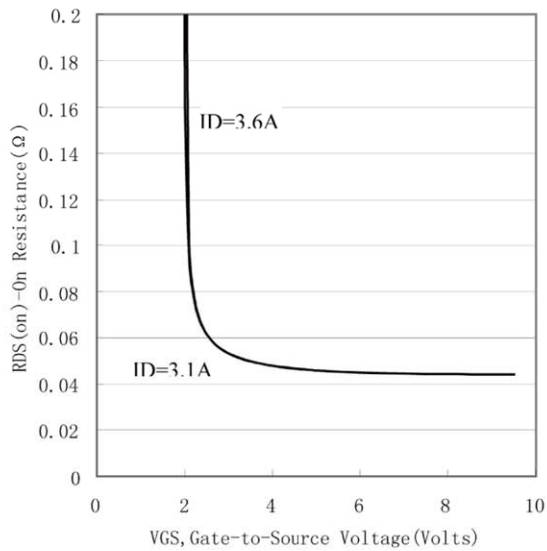

Figure 6. On-Resistance vs. Drain Current
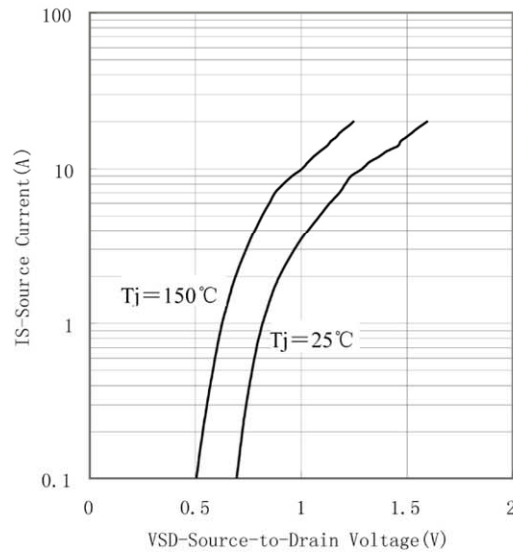

Figure 7. On-Resistance vs. Gate-to-Source
Voltage

Figure 8. Source-Drain Diode Forward
Voltage

SHIKE MAKE CONSCIOUS PRODUCT
CONSCIOUS PRODUCTS BEGIN WITH CONSCIOUS PEOPLE
REV.07

www.shike.tw

单击下面可查看定价，库存，交付和生命周期等信息

>>SHIKUES(时科)